

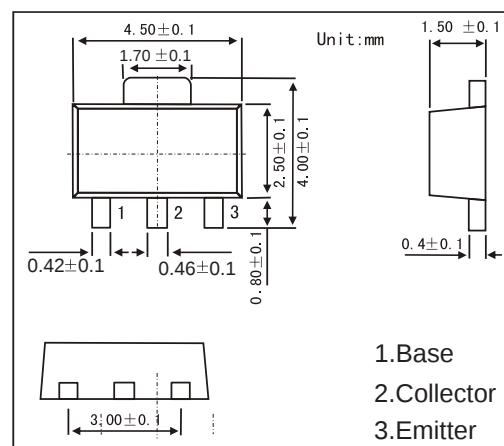
SOT-89 Plastic-Encapsulate Transistors

Features

- Small Flat Package
- High Current Application
- High Transition Frequency
- PNP Transistors

MECHANICAL DATA

- Case style: SOT-89 molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-35	V
Collector - Emitter Voltage	V_{CE0}	-30	
Emitter - Base Voltage	V_{EB0}	-5	
Collector Current - Continuous	I_C	-800	mA
Collector Power Dissipation	P_C	500	mW
Thermal Resistance From Junction to Ambient	$R_{\theta JA}$	250	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature range	T_{stg}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -1mA, I_E = 0$	-35			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -10mA, I_B = 0$	-30			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -1mA, I_C = 0$	-5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -35V, I_E = 0$			-0.1	uA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -20mA$			-0.7	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500mA, I_B = -20mA$			-1.2	
Base - emitter voltage	V_{BE}	$V_{CE} = -1V, I_C = -10mA$	-0.5		-0.8	
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -100mA$	100		320	
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -700mA$	35			
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		19		pF
Transition frequency	f_T	$V_{CE} = -5V, I_C = -10mA$		120		MHz